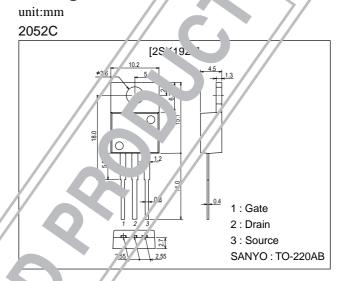


Features

- · Low ON resistance.
- · Ultrahigh-speed switching.
- · High-speed diode (trr=120ns).

Package Dimensions



Specifications

Absolute Maximum Ratings at $Ta = 25^{\circ}C$

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		600	V
Gate-to-Source Voltage	V/38/3		±30	V
Drain Current (DC)	10		4	А
Drain Current (pulse)	I _{DP}		16	А
Allowable Power Dissipation	Po		1.75	W
	PD TC=20 J		60	W
Channel Temperature	TCri		150	°C
Storage Temperature	Tstg	//	-55 to +150	°C

Electrical Characteristics at Ta = `5°C

Parameter	J	Conditions		Ratings		
			min	typ	max	Unit
Drain-to-Source Breakdowr Vrutage		=10mA, V _{GS} =0	600			V
Zero-Gate Votlage Drain Current	I _{DSS} V _E	DS=480V, VGS=0			1.0	mA
Gate-to-Source Leakage Surrent	IGSS VC	_{GS} =±30V, V _{DS} =0			±100	nA
Cutoff Voltage	VrJS(off) VE	DS=10V, ID=1mA	2.0		3.0	V
Forward Transfer Acimittance	yfs V	_{DS} =10V, I _D =2A	1.8	3.5		S
Static Drain-to-Source On Late Posistance	KDS(on)	=2A, V _{GS} =10V		1.8	2.4	Ω
(Note) Be car eff (l in hand) ~ 28 1923	pe av se it has no prot	tection diode between gate and source	÷	Contin	ued on n	ext nage

(Note) Be callef if in handline e 28 1923 be call se it has no protection diode between gate and source

Continued on next page.

- Any an all SAN7C products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your SANYO representative nearest you before using any SANYC products described or contained herein in such applications.
- SANYO assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges,or other parameters) listed in products specifications of any and all SANYO products described or contained herein.

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Continued from preceding page.

Parameter	Symbol	Conditions		Ratings		Unit
Input Capacitance	Ciss	V _{DS} =20V, f=1MHz		700		pF
Output Capacitance	Coss	V _{DS} =20V, f=1MHz		90		pF
Reverse Transfer Capacitance	Crss	V _{DS} =20V, f=1MHz		30		pF
Turn-ON Delay Time	td(on)	See specified Test Circuit.		13		ns
Rise Time	tr	See specified Test Circuit.		15		ns
Turn-OFF Delay Time	td(off)	See specified Test Circuit.		160		ns
Fall Time	tf	See specified Test Circuit.		40	\sim	ns
Diode Forward Voltage	V _{SD}	IS=4A, VGS=0			15	V
Diode Reverse Recovery Time	trr	I _S =4A, di/dt=100A/µs		.50	7	ns

Switching Time Test Circuit

